

ABSTRACT OF THE DISCLOSURE

A semiconductor device is provided with a semiconductor substrate, a gate insulation film formed on the semiconductor substrate, a gate electrode formed on the gate insulation film and having a portion increasing upward in the length along a gate length direction, a side wall formed on a side surface of the gate electrode so as to be covered behind a top part of the gate electrode as seen in plan view, and an interlayer insulation film covering the gate electrode. The side wall is in contact with the interlayer insulation film.

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